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LIST OF SYMBOLS

I_D	-	Standby current
V_{BR}	-	Voltage breakdown
C	-	Capacitance
L	-	Inductance
R	-	Resistor
V_{WM}	-	Rated standoff voltage
I_{FSM}	-	Rated forward surge current
V_{FS}	-	Forward voltage
V_C	-	Voltage clamping
t_f	-	Front time wave
t_t	-	Tail time wave
Ω	-	ohm

LIST OF ABBREVIATIONS

TVS	-	Transient Voltage Suppression
MIGe	-	Multiple Impulse Generator
SPD	-	Surge Protective Devices
MOV	-	Metal Oxide Varistor
GDT	-	Gas Discharge Tube
AC	-	Alternating current
DC	-	Direct current

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